Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	10	(("6514830") or ("6350639") or ("6025240") or ("6187644") or ("6294432")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/13 17:37
S2	6	("3673679" | "4470191" | "4830974" | "5296401" | "5427971" | "6191044").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:09
S3	1	("6350639").URPN.	USPAT	OR	ON	2005/10/13 14:09
S4	6	("3673679" | "4470191" | "4830974" | "5296401" | "5427971" | "6191044").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:08
S5	7	("3673679" | "4470191" | "4830974" | "5296401" | "5427971" | "6191044").PN. OR ("6350639").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:08
S6	4	("4558338" | "5834817" | "5937299" | "6013570").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/13 14:12
S7	1293	(438/301).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/13 16:23
S8	415	S7 and (ldd (lightly adj doped adj (source drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 17:38
S9	0	("2005/0202642").URPN.	USPAT	OR	ON	2005/10/13 17:35
S10	651	(438/302).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/13 17:37
S11	270	S10 and (ldd (lightly adj doped adj (source drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:39

S12	4893	((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/16 17:56
S13	2179	S12 and (ldd (lightly adj doped adj (source drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:39
S14	2147	S13 and ((ion impurit$3 atom) nera4 implant$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:41
S15	641	S14 and (rie (react$4 adj ion adj etch$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:35
S16	74	S15 and (mosfet and nmos and pmos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:45
S17	0	S15 and (Cl and HBr and O and CF and He)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:36
S18	2	S15 and (Cl and HBr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:55
S19	289	S15 and ((lpcvd (low adj pressure adj chemical adj vapor adj deposit$3)) pecvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:02

S20	294	S15 and ((lpcvd (low adj pressure adj chemical adj vapor adj deposit$3)) pecvd (plasma adj enhanced adj chemical adj vapor adj deposit$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:03
S21	65	S20 and ((arsine phosphine) and (silane disilane))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:04
S22	0	("2005/0095799").URPN.	USPAT	OR	ON	2005/10/14 14:15
S23	5	S21 and ((SiN (silicon adj nitride)) and (SiNO (silicon adj oxynitride)) and (SiO (silicon adj oxide)))	USPAT	OR	ON	2005/10/14 14:18
S24	4893	((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/16 17:57
S25	1377	S24 and ((pattern$3 shap$3) near3 (mask$3 resit$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 17:58
S26	3850	S24 and ((remov$3 delet$3) nera3 (pattern$3 shap$3) near3 (mask$3 resit$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:00
S27	154	S24 and ((remov$3 delet$3) near3 (pattern$3 shap$3) near3 (mask$3 resit$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:00
S28	19	S27 and (hot near3 (phosphor$3 adj acid))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:01
S29	1044	S24 and (rie (react$4 adj ion adj etch$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:46

S30	0	S29 and (Cl and HBr and O and CF and He and N)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:38
S31	0	S29 and (Cl and HBr and CF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:37
S32	0	S29 and (HBr and CF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:37
S33	1	S29 and (Chlori$3 and HBr and oxid$3 and (carbon adj tetrafluoride) and helium and nitrid$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:47
S34	87671	mosfet (metal adj oxide adj semiconductor adj field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:45
S35	5539	S34 and (rie (react$4 adj ion adj etch$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:46
S36	2	S35 and (Chlori$3 and HBr and oxid$3 and (carbon adj tetrafluoride) and helium and nitrid$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 18:47